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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0018			
I _D (A)	200			
Configuration	Single			
Package	TO-263-7L			

FEATURES

• TrenchFET® power MOSFET

N-Channel MOSFET

- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	40		
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	- I _D	200	А	
	T _C = 125 °C		192		
Continuous Source Current (Diode Condu	ction) ^a	I _S	200		
Pulsed Drain Current b		I _{DM}	600		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	85		
Single Pulse Avalanche Energy	L=U.I IIIH	E _{AS}	361	mJ	
	T _C = 25 °C	D	375	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	125		
Operating Junction and Storage Temperature Range		T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	R_{thJA}	40	°C/W	
ınction-to-Case (Drain)		R_{thJC}	0.4	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = 250 μA		3.0	3.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	200	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 30 A	=.	0.0015	0.0018	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0028	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	=.	-	0.0034	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	198	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			1	13 880	17 350	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = 25 V, f = 1 MHz$		1414	1770	pF
Reverse Transfer Capacitance	C _{rss}			'n	840	1050	1
Total Gate Charge ^c	Qg			i	206	310	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 120 \text{ A}$	1	50	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	44	=	
Gate Resistance	R_g		f = 1 MHz		0.8	1.8	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	26	39	
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 0.17 Ω I_D \cong 120 A, V_{GEN} = 10 V, R_g = 1 Ω		'n	21	32	ns
Turn-Off Delay Time ^c	t _{d(off)}			1	68	102	
Fall Time ^c	t _f			ı	12	18	
Source-Drain Diode Ratings and Chara	cteristics b						
Pulsed Current ^a	I _{SM}			-	-	600	Α
Forward Voltage	V _{SD}	I _F = 80 A, V _{GS} = 0 V		_	0.86	1.5	V

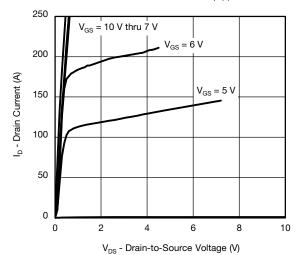
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

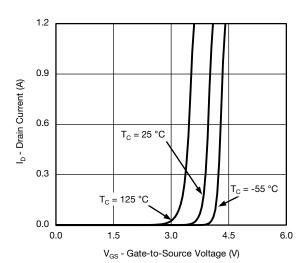
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



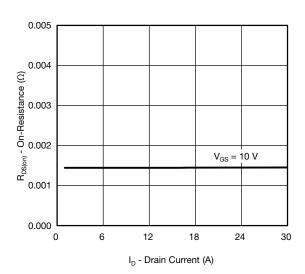
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



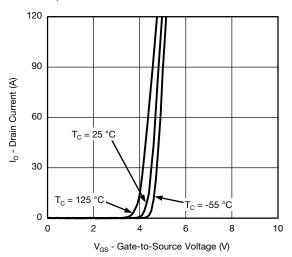
Output Characteristics



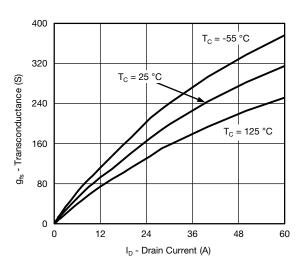
Transfer Characteristics



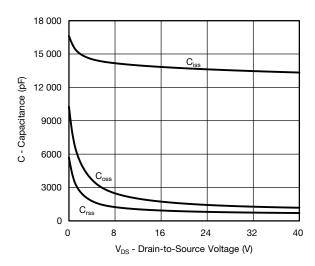
On-Resistance vs. Drain Current



Transfer Characteristics



Transconductance

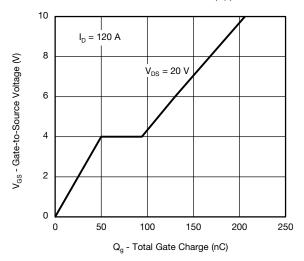


Capacitance

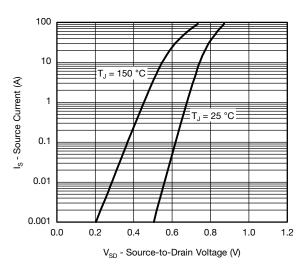
For technical questions, contact: automostechsu



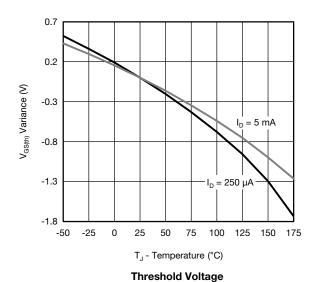
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

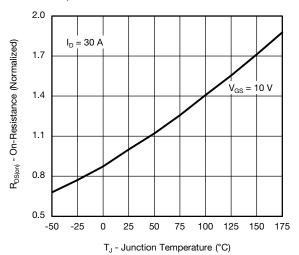


Gate Charge

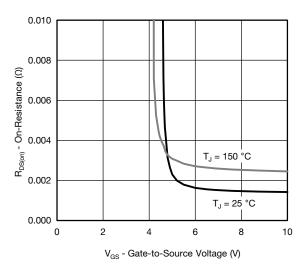


Source Drain Diode Forward Voltage

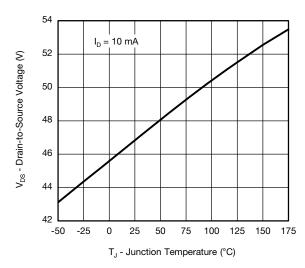




On-Resistance vs. Junction Temperature



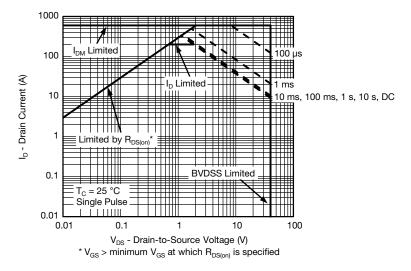
On-Resistance vs. Gate-to-Source Voltage



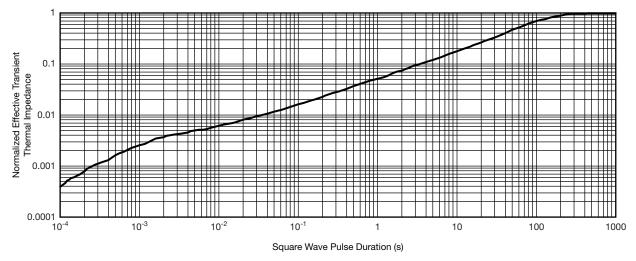
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



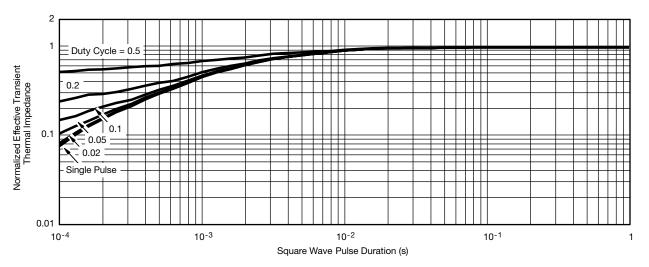
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267184.



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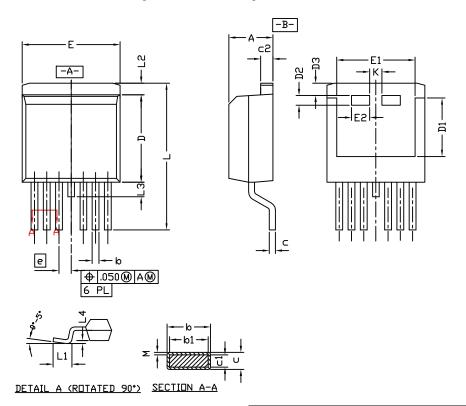
REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R _g minimum limit		

Note

a. As of April 2014



D²PAK (TO-263-7L) Case Outline



Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

	INCHES		MILLIMETERS	
DIM.	MIN.	MAX.	MIN.	MAX.
Α	0.160	0.190	4.064	4.826
b	0.020	0.039	0.508	0.990
b1	0.020	0.035	0.508	0.889
b2	0.045	0.055	1.143	1.397
c* SUB	0.012	0.018	0.305	0.457
c* SUM	0.022	0.028	0.559	0.711
c1	0.018	0.025	0.457	0.635
c2	0.045	0.055	1.143	1.397
D	0.340	0.380	8.636	9.652
D1	0.220	0.240	5.588	6.096
D2	0.038	0.042	0.965	1.067
D3	0.045	0.055	1.143	1.397
Е	0.380	0.410	9.652	10.414
E1	0.245	-	6.223	-
E2	0.072	0.078	1.829	1.981
е	0.050	BSC	1.27 BSC	
K	0.045	0.055	1.143	1.397
L	0.575	0.625	14.605	15.875
L1	0.090	0.110	2.286	2.794
L2	0.040	0.055	1.016	1.397
L3	0.050	0.070	1.270	1.778
L4	0.010 BSC		0.254 BSC	
М	-	0.002	-	0.050
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006				



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